

Plasma Etching System

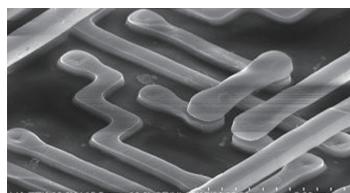
The RIE process is a chemical physical etching process, and it is the most important process for constructing various films in semiconductor manufacturing. This system can control the gas and plasma process, can perfectly produce high-quality thin films.



RIE

RIE/ICP-RIE

- Flexible substrate size up to 12 inch in diameter.
- Single wafer or multi wafers.
- Excellent thin-film uniformity of less than $\pm 5\%$.
- Mass flow controllers with highly uniform gas distribution up to 6 gas lines.
- Substrate chuck heating up to 400°C or cooling down to -20°C by stable process temperatures.



Options

- Electrostatic Chuck.
- Endpoint monitors (OES, laser) compatibility.
- Cluster allows for vacuum transfer of substrates.

Applications

- Silicon and silicon-based compounds (SiO_2 , Si_3N_4).
- MEMS.
- Metal, silicon, resist etching.



ICP-RIE

